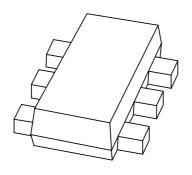
### DISCRETE SEMICONDUCTORS

## DATA SHEET



# PMEG2005AEV; PMEG3005AEV; PMEG4005AEV

Very low V<sub>F</sub> MEGA Schottky barrier rectifiers

**Product specification** 

2003 Aug 20





### Very low V<sub>F</sub> MEGA Schottky barrier rectifiers

## PMEG2005AEV; PMEG3005AEV; PMEG4005AEV

#### **FEATURES**

- · Very low forward voltage
- · High surge current
- Ultra small plastic SMD package.

#### **APPLICATIONS**

- · Low voltage rectification
- High efficiency DC/DC conversion
- Voltage clamping
- · Inverse polarity protection
- Low power consumption applications.

#### **DESCRIPTION**

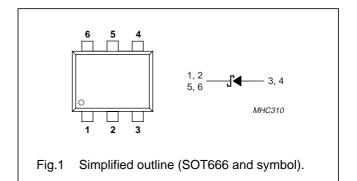
Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOT666 ultra small SMD plastic package.

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
I <sub>F</sub>	forward current	0.5	Α
$V_R$	reverse voltage		
	PMEG2005AEV	20	V
	PMEG3005AEV	30	٧
	PMEG4005AEV	40	V

#### **PINNING**

PIN	DESCRIPTION
1	cathode
2	cathode
3	anode
4	anode
5	cathode
6	cathode



#### **MARKING**

TYPE NUMBER	MARKING CODE
PMEG2005AEV	G1
PMEG3005AEV	G2
PMEG4005AEV	G3

#### **RELATED PRODUCTS**

TYPE NUMBER	DESCRIPTION	FEATURE
PMEGxx05AEA	0.5 A; 20/30/40 V very low V <sub>F</sub> MEGA Schottky rectifier	SOD323 (SC-76) package
PMEG2005EB	0.5 A; 20 V very low V <sub>F</sub> MEGA Schottky rectifier	SOD523 (SC-79) package
PMEG2010EA	1 A; 20 V very low V <sub>F</sub> MEGA Schottky rectifier	higher forward current

### Very low V<sub>F</sub> MEGA Schottky barrier rectifiers

PMEG2005AEV; PMEG3005AEV; PMEG4005AEV

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>R</sub>	continuous reverse voltage				
	PMEG2005AEV		_	20	V
	PMEG3005AEV		_	30	V
	PMEG4005AEV		_	40	V
I <sub>F</sub>	continuous forward current	note 1	_	0.5	Α
I <sub>FRM</sub>	repetitive peak forward current	$t_p \le 1 \text{ ms}; \ \delta \le 0.5; \ \text{note 2}$	_	3.5	А
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 8 ms; square wave; note 2	_	10	Α
T <sub>j</sub>	junction temperature	note 3	_	150	°C
T <sub>amb</sub>	operating ambient temperature	note 3	-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

#### **Notes**

- 1. Refer to SOT666 standard mounting conditions.
- 2. Only valid if pins 3 and 4 are connected in parallel.
- For Schottky barrier diodes thermal runaway has to be considered, as in some applications, the reverse power losses
   (P<sub>R</sub>) are a significant part of the total power losses. Nomograms for determination of the reverse power losses P<sub>R</sub>
   and I<sub>F(AV)</sub> rating will be available on request.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to	in free air; notes 1 and 2	405	K/W
	ambient	in free air; notes 2 and 3	215	K/W
R <sub>th j-s</sub>	thermal resistance from junction to soldering point	note 4	80	K/W

#### **Notes**

- 1. Refer to SOT666 standard mounting conditions.
- For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses
   P<sub>R</sub> are a significant part of the total power losses. Nomograms for determination of the reverse power losses P<sub>R</sub> and
   I<sub>F(AV)</sub> rating will be available on request.
- 3. Device mounted on an FR4 printed-circuit board with copper clad  $10 \times 10$  mm.
- 4. Solder point of cathode tab.

## Very low V<sub>F</sub> MEGA Schottky barrier rectifiers

PMEG2005AEV; PMEG3005AEV; PMEG4005AEV

#### **ELECTRICAL CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

CVMBOL	DADAMETED	CONDITIONS	PMEG2005AEV		PMEG3005AEV		PMEG4005AEV		LINUT
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	TYP.	MAX.	TYP.	MAX.	UNIT
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 0.1 mA	90	130	90	130	95	130	mV
		I <sub>F</sub> = 1 mA	150	190	150	200	155	210	mV
		I <sub>F</sub> = 10 mA	210	240	215	250	220	270	mV
I <sub>F</sub>		I <sub>F</sub> = 100 mA	280	330	285	340	295	350	mV
	$I_F = 500 \text{ mA}$		355	390	380	430	420	470	mV
I <sub>R</sub> continuous reverse \		V <sub>R</sub> = 10 V; note 1	15	40	12	30	7	20	μΑ
	current	V <sub>R</sub> = 20 V; note 1	40	200	_	_	_	_	μΑ
		V <sub>R</sub> = 30 V; note 1	_	_	40	150	_	_	μΑ
		V <sub>R</sub> = 40 V; note 1	_	_	_	_	30	100	μΑ
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz	66	80	55	70	43	50	pF

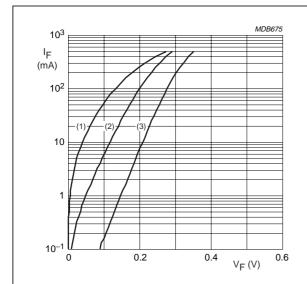
#### Note

<sup>1.</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

## Very low V<sub>F</sub> MEGA Schottky barrier rectifiers

## PMEG2005AEV; PMEG3005AEV; PMEG4005AEV

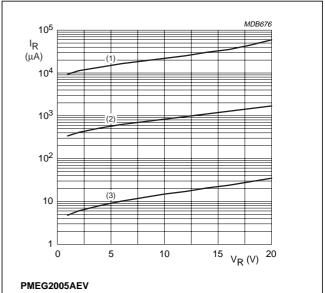
#### **GRAPHICAL DATA**



#### PMEG2005AEV

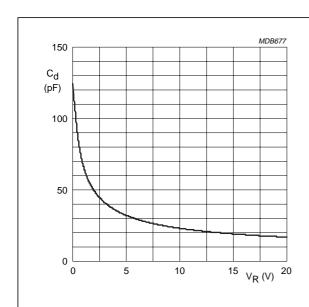
- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \,^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.2 Forward current as a function of forward voltage; typical values.



- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.3 Reverse current as a function of reverse voltage; typical values.



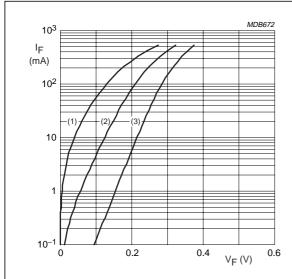
#### PMEG2005AEV

 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}.$ 

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

## Very low V<sub>F</sub> MEGA Schottky barrier rectifiers

## PMEG2005AEV; PMEG3005AEV; PMEG4005AEV



#### PMEG3005AEV

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.5 Forward current as a function of forward voltage; typical values.

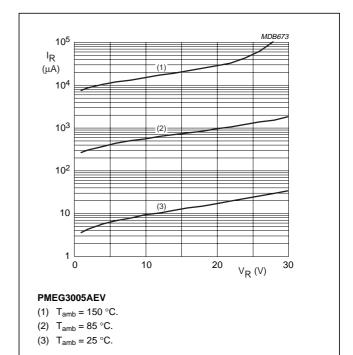
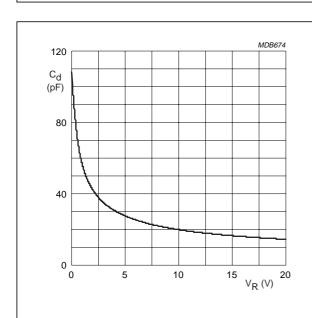


Fig.6 Reverse current as a function of reverse

voltage; typical values.



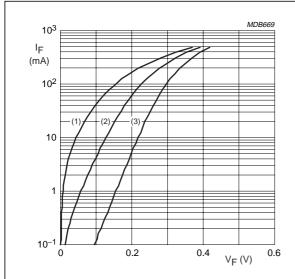
#### PMEG3005AEV

 $f = 1 \text{ MHz}; T_{amb} = 25 \, ^{\circ}\text{C}.$ 

Fig.7 Diode capacitance as a function of reverse voltage; typical values.

## Very low V<sub>F</sub> MEGA Schottky barrier rectifiers

## PMEG2005AEV; PMEG3005AEV; PMEG4005AEV



#### PMEG4005AEV

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.8 Forward current as a function of forward voltage; typical values.

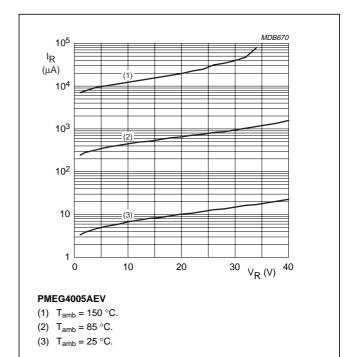
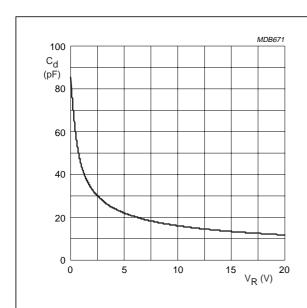


Fig.9 Reverse current as a function of reverse voltage; typical values.



#### PMEG4005AEV

 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}.$ 

Fig.10 Diode capacitance as a function of reverse voltage; typical values.

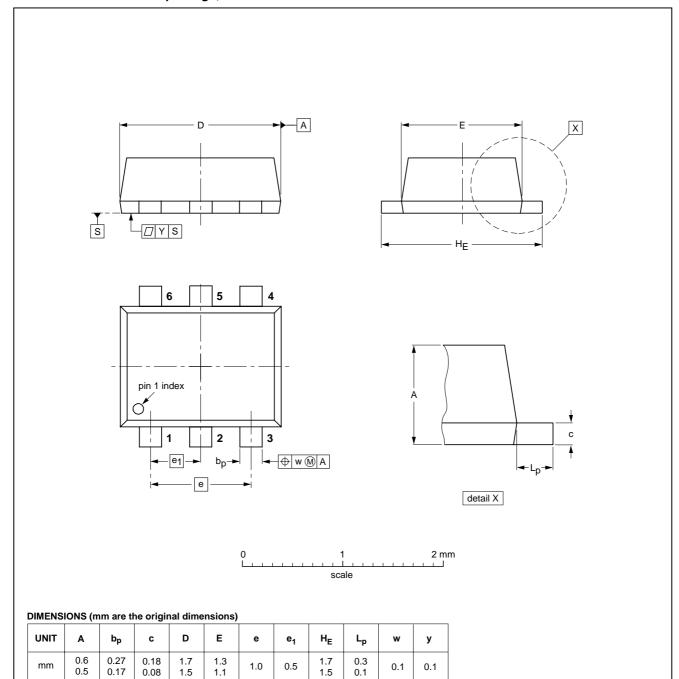
Very low V<sub>F</sub> MEGA Schottky barrier rectifiers

PMEG2005AEV; PMEG3005AEV; PMEG4005AEV

#### **PACKAGE OUTLINE**

Plastic surface mounted package; 6 leads

SOT666



OUTLINE	REFERENCES			EUROPEAN		ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT666						<del>-01-01-04</del> 01-08-27	

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### Very low V<sub>F</sub> MEGA Schottky barrier rectifiers

## PMEG2005AEV; PMEG3005AEV; PMEG4005AEV

#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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